

# Power Conversion for HEP Using Piezoelectric Elements

## Coordinating Panel for Advanced Detectors Workshop

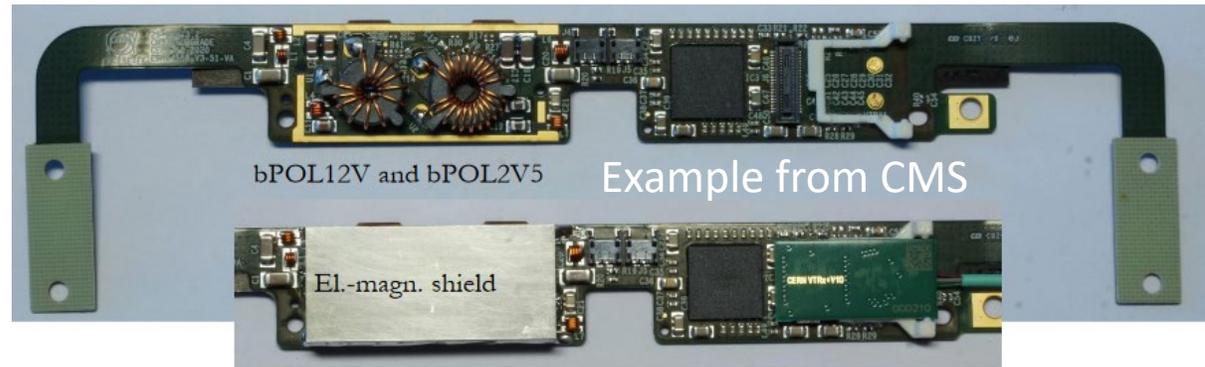
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University of Pennsylvania, 7 October 2025

# Problem

- DC-DC converters in HEP often use inductors
  - These generate electromagnetic interference (EMI) and must be shielded if in a magnetic field
  - They are physically large
- Converter may need to be radiation tolerant
- May not be desirable to have a large number of discrete components
- Other powering schemes:
  - Serial powering\* for low cable mass – constant current low dropout regulator, chip fault handling
  - Linear regulators where a specific use case exists
- Future detectors may need highly miniaturized on-chip or on-module converters

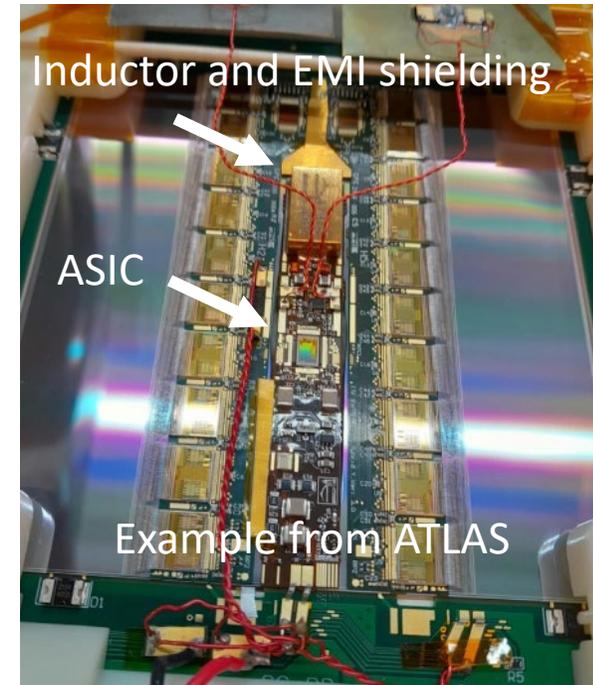


Michelis, S., "Powering Next Generation Detector Systems",  
Implementing DRD7: an R&D Collaboration on Electronics and On-detector Processing, 2nd Workshop,  
[https://indico.cern.ch/event/1318635/contributions/5551795/attachments/2720651/4726975/WP7.1b\\_2023\\_09\\_25.pdf](https://indico.cern.ch/event/1318635/contributions/5551795/attachments/2720651/4726975/WP7.1b_2023_09_25.pdf)



FEAST/bPOL,  
0.35 $\mu$ m rad hard

F. Faccio *et al.*, "FEAST2: A Radiation and Magnetic Field Tolerant Point-of-Load Buck DC/DC Converter,"  
2014 IEEE Radiation Effects Data Workshop (REDW),  
Paris, France, 2014, pp. 1-7, doi:  
10.1109/REDW.2014.7004569



Example from ATLAS

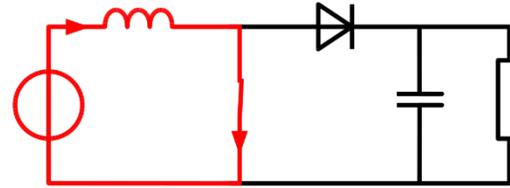
\*Chan, Jay, "Serial Powering for ATLAS ITk Pixel Modules",  
10th International Workshop on Semiconductor Pixel Detectors for Tracking and Imaging (PIXEL 2022), Santa Fe, USA, 11 - 16  
Dec 2022, <https://cds.cern.ch/record/2845615>

Cold Noise Studies, ITk Strips Barrel Modules PRR,  
<https://indico.cern.ch/event/1269138/contributions/5350778/attachments/2642336/4577685/affolder-CN-modulePRR-v4.pdf>

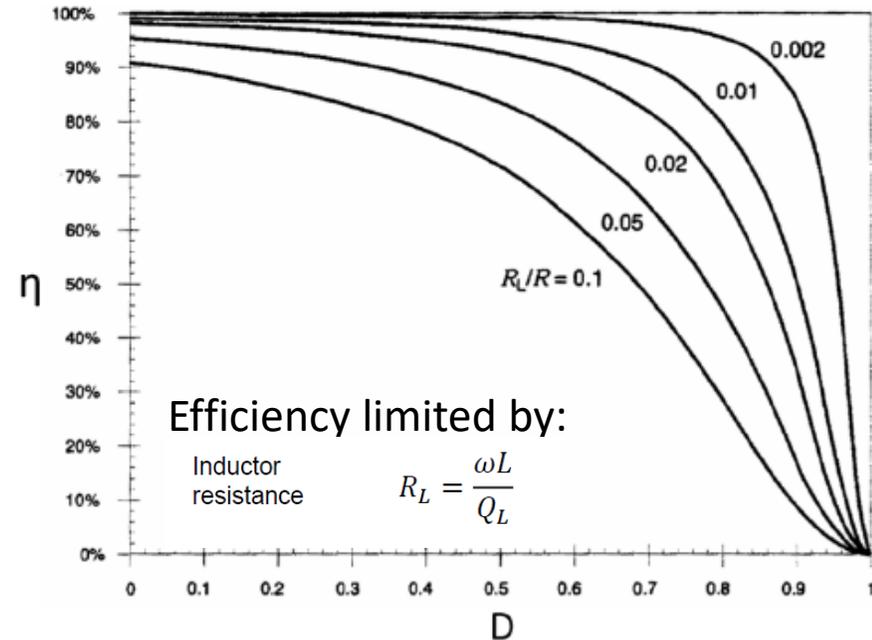
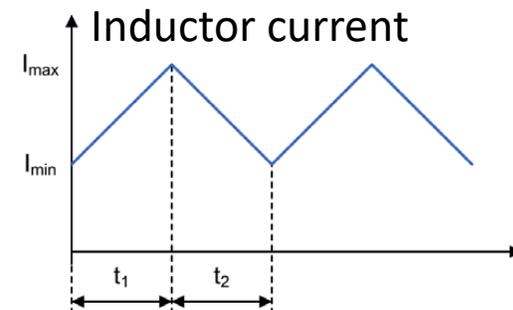
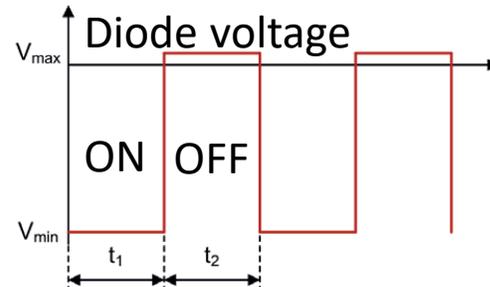
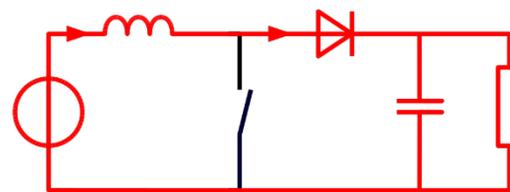
# Inductive DC-DC Converter

- Energy stored in **magnetic field**
- MANY topologies! (boost, buck, buck-boost ...)
- Advantages:
  - simplest and lowest cost (usually)
- Disadvantages:
  - Inductors are lossy
    - Resistance dissipates some energy as heat
    - Magnetic hysteresis
  - Quality inductors are **difficult to miniaturize**
    - $L$ ,  $Q$  (and  $R_L$ ) decrease with volume
  - Hard switched -> electromagnetic Interference (EMI)
  - Discontinuous conduction mode and synchronous rectification can be used, but are more complex

On-State (boost example)



Off-State



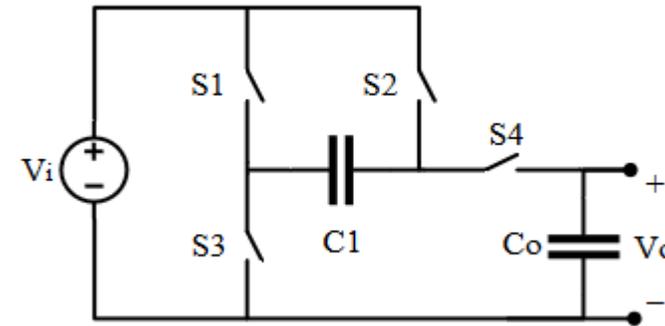
R. W Erickson, "DC-DC Power Converters," J. Webster (ed.), Wiley Encyclopedia of Electrical and Electronics Engineering, pp. 1-18, 2007.



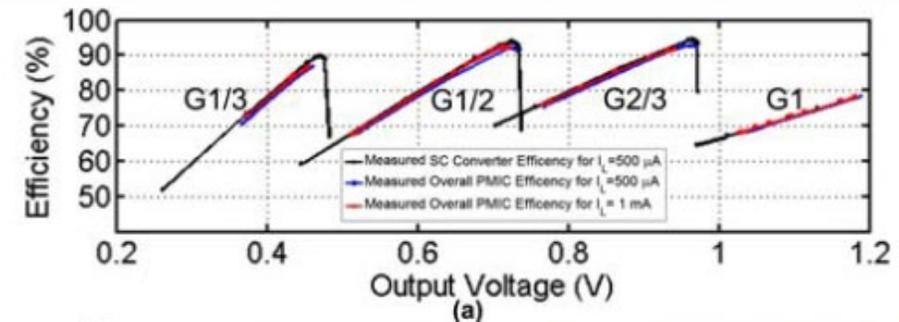
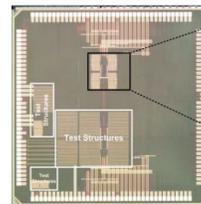
Image: [https://en.wikipedia.org/wiki/Boost\\_converter](https://en.wikipedia.org/wiki/Boost_converter)

# Switched Capacitor (SC) Converter

- Charge pump principle, descended from voltage doubler
  - Energy stored in **electric field** instead of magnetic
  - Also MANY topologies
- Advantages:
  - Higher **energy density** than inductors
  - **Monolithic integration into ASICs** (compatible with common process nodes)
  - **Lower EMI** than inductors
- Disadvantages:
  - Voltage **regulation is more difficult** than inductor based converters
    - Discrete gain ratios (unless dynamic topology change)
    - Duty cycle does not linearly relate to output voltage
    - Difficult to control charge balance with multiple capacitors
  - FET switching losses (resistive, gate drive)
  - Bottom plate parasitic capacitance to substrate limits efficiency



de Souza, A.F., Tolofi, F.L., Ribeiro, E.R., "Switched Capacitor DC-DC Converters: A Survey on the Main Topologies, Design Characteristics, and Applications", MDPI Energies 2021, 14(8), 2231; <https://doi.org/10.3390/en14082231>



El-Damak, D., S. Bandyopadhyay, and A. P. Chandrakasan. "A 93% Efficiency Reconfigurable Switched-Capacitor DC-DC Converter Using on-Chip Ferroelectric Capacitors." 2013 IEEE International Solid-State Circuits Conference Digest of Technical Papers (February 17-21, 2013), San Francisco, CA.



Inductors and capacitors are the only energy storage elements

Is this the best we can do?

Only if we think strictly in the electrical domain...

# Modeling Piezoelectric Elements

- The mechanical mass, spring, damper model can be transformed to an electrical RLC model
  - Damping -> resistance
  - Spring (stiffness) -> capacitance
  - Mass -> inductance
- Transform is proportional to Young's modulus, and the strain coefficient of the material

$$\Gamma = d_{31} E \pi r^2$$

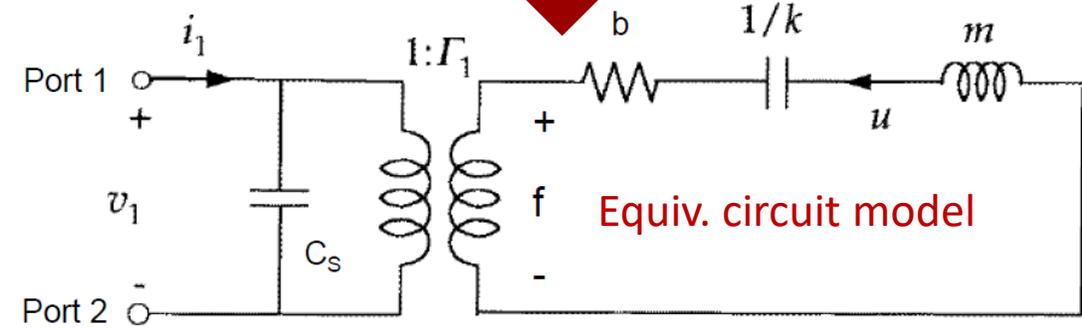
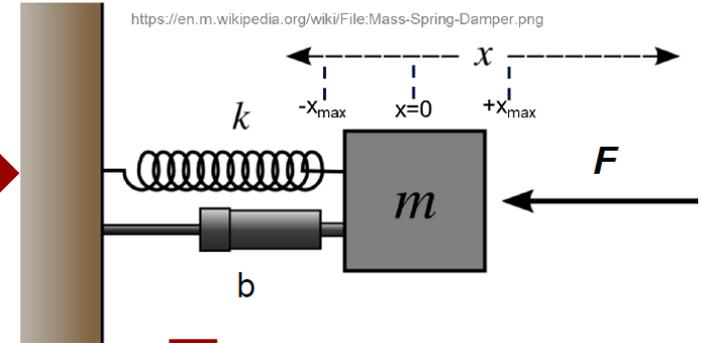
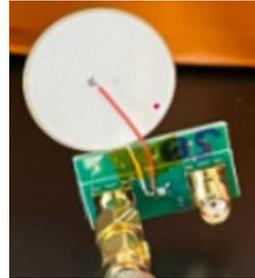
Strain coeff. (pm/V)      Young's modulus (GPa)

$$R_x = \frac{b}{\Gamma^2}$$

$$L_x = \frac{m}{\Gamma^2}$$

$$C_x = \frac{\Gamma^2}{k}$$

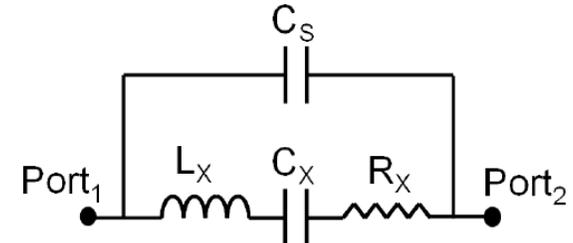
- Origin of larger Q and L (per volume) in piezoelectric element is the effective stiffness and mass of the material



H.A.C. Tilmans, "Equivalent Circuit Representation of Electromechanical Transducers: I. Lumped-parameter Systems", J. Micromech. Microeng. 6 157, 1996, doi: 10.1088/0960-1317/6/1/036  
Illustration adapted by Troy Olsson



Electrodes →  
Energy storage →



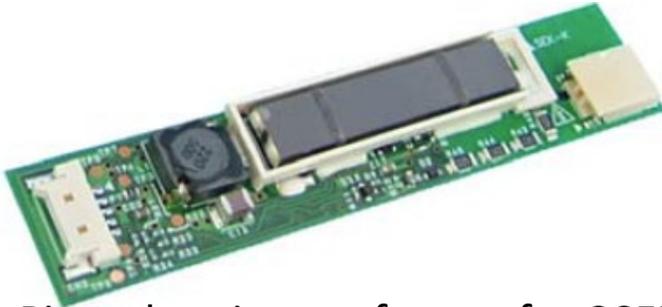
Microresonator Butterworth Van Dyke (BVD) equivalent circuit model

(Image: Troy Olsson)



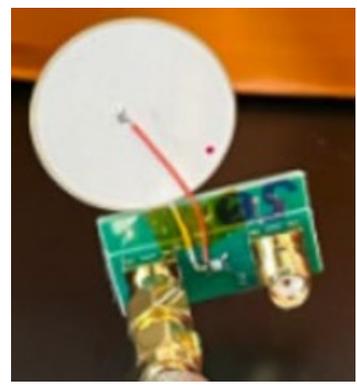
# Piezoelectric (PR) DC-DC Converter

- Energy storage is **mechanical**, not magnetic/electric field
  - **Low EMI**
  - Potentially radiation tolerant
- Long history of piezoelectrics in power conversion\*
- But recent advances in resonant PR converters are promising\*\*
  - “Soft-switched” (sinusoidal current)
  - **Wide conversion ratios**
- For equivalent inductor volume:
  - **High quality factor (Q)**
  - **Large inductance**
  - Low series resistance
- Potentially integrated into ASICs

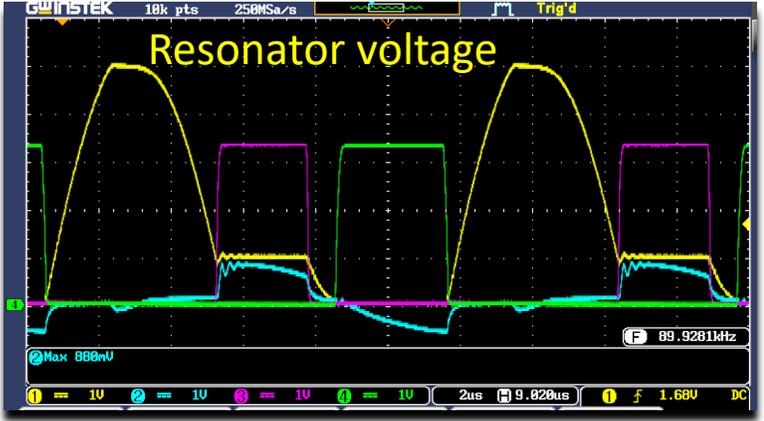


Piezoelectric transformer for CCFL

"Piezoelectric Transformers: An Historical Review"  
<https://www.mdpi.com/2076-0825/5/2/12>



Commercial lead zirconate titanate (PZT) resonator



A piezoelectric conversion cycle using PZT resonator

\*Carazo, A., Piezoelectric Transformers: An Historical Review ", MDPI *Actuators* 2016, 5(2), 12; <https://doi.org/10.3390/act5020012>

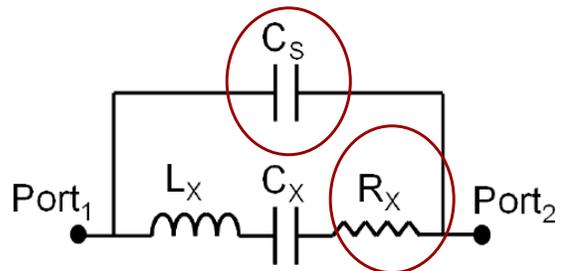
\*\*B. Pollet, G. Despesse and F. Costa, "A New Non-Isolated Low-Power Inductorless Piezoelectric DC–DC Converter," in *IEEE Transactions on Power Electronics*, vol. 34, no. 11, pp. 11002-11013, Nov. 2019, doi: 10.1109/TPEL.2019.2900526.

\*\*J. D. Boles, J. J. Piel and D. J. Perreault, "Enumeration and Analysis of DC–DC Converter Implementations Based on Piezoelectric Resonators," in *IEEE Transactions on Power Electronics*, vol. 36, no. 1, pp. 129-145, Jan. 2021, doi: 10.1109/TPEL.2020.3004147.

\*\*J. D. Boles, J. E. Bonavia, J. H. Lang and D. J. Perreault, "A Piezoelectric-Resonator-Based DC–DC Converter Demonstrating 1 kW/cm Resonator Power Density," in *IEEE Transactions on Power Electronics*, vol. 38, no. 3, pp. 2811-2815, March 2023, doi: 10.1109/TPEL.2022.3217773.

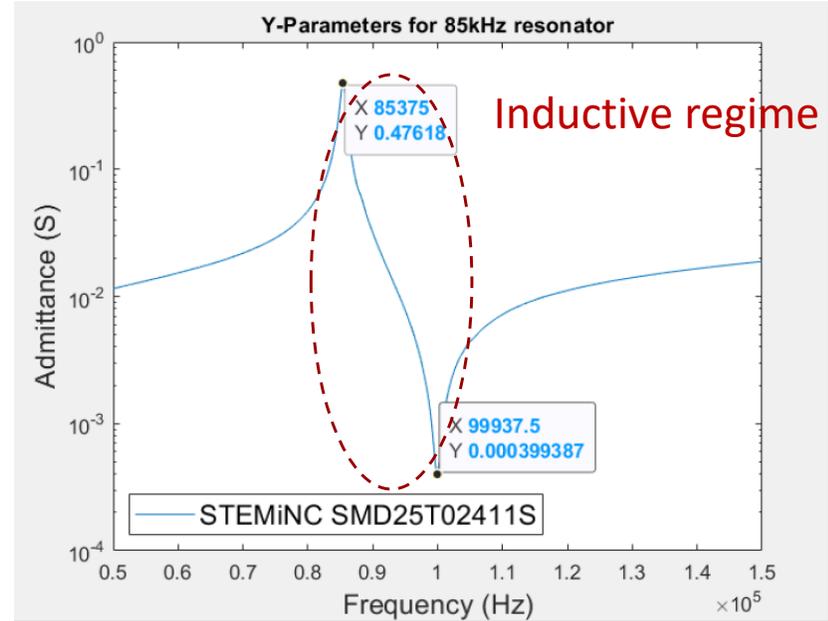
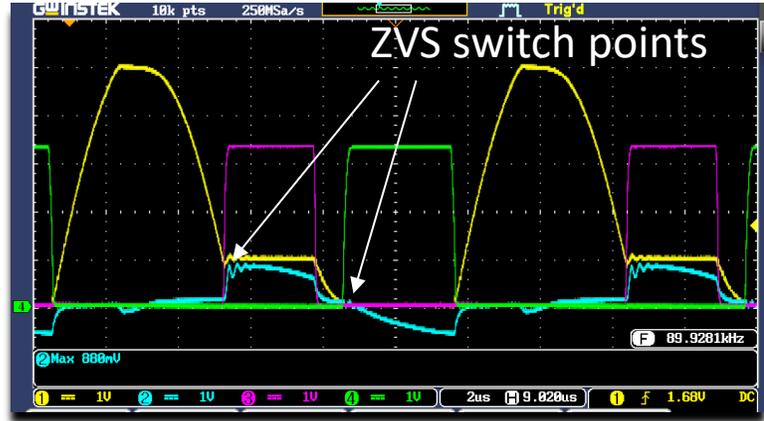
# PR Limitations

- Shunt  $C_s$
- Need low series resistance  $R_x$  to maximize voltage gain efficiency
- Operates near resonance
  - Load change  $\rightarrow$  frequency change
- Control depends on **zero volt switching (ZVS)**
  - Control must operate at higher frequencies if resonator is miniaturized



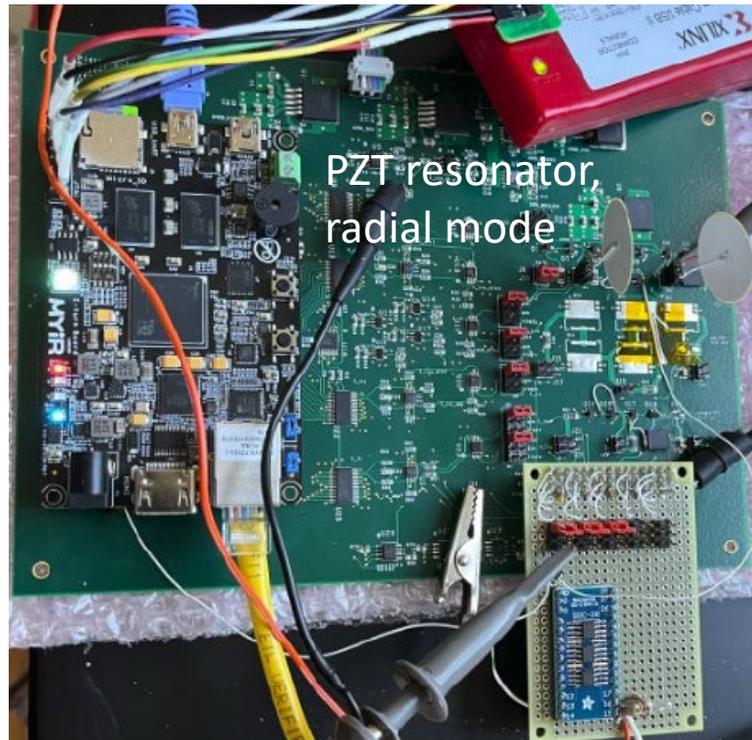
Microresonator Butterworth Van Dyke (BVD) equivalent circuit model  
(illustration courtesy Troy Olsson)

$$R_x = \frac{1}{\omega_0 C_s K^2 Q}$$



# Prototyping

- 1-5V piezoelectric DC-DC boost conversion demonstrated with macroscale PZT prototypes
  - Application of boost converters: extend to SiPMs (~50V)
  - Also investigating buck
- Questions:
  - Can we continue to miniaturize?
  - What are ultimate performance limits in buck and boost mode?
  - EMI, radiation and magnetic tolerant DC-DC converters for HEP?



# Power converter research in general

- Efficient energy storage elements (resonators in our case)
- Efficient switches
- Robust control schemes for wide load ranges

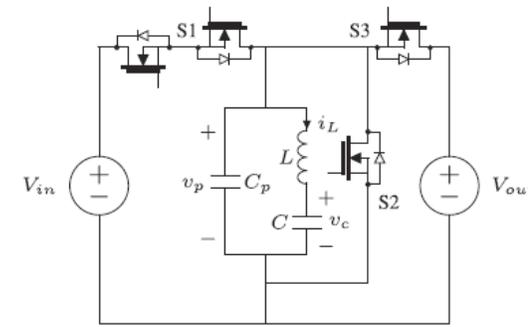
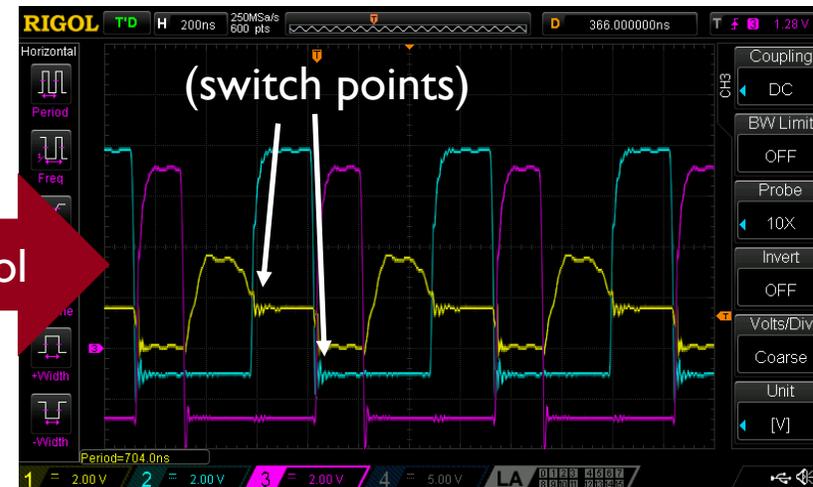


Image: J. D. Boles, J. J. Piel and D. J. Perreault, "Enumeration and Analysis of DC-DC Converter Implementations Based on Piezoelectric Resonators," in *IEEE Transactions on Power Electronics*, vol. 36, no. 1, pp. 129-145, Jan. 2021, doi: 10.1109/TPEL.2020.3004147.



Digital control



# Analog v. power electronics

- Analog:

- Transistor is biased at an operating point
  - Not always considering switching loss,  $R_{on}$
- Think of FET as a voltage controlled device
- Relatively small drain currents ( $\mu A$  or  $mA$ )
- Relatively low voltages (under  $\sim 3.3V$ )
- Signals almost always referenced to ground

- Power:

- Transistor is either completely on or off
  - Switching loss extremely important
- Gate current is important
- Relatively large drain currents (tens of Amps)
- Relatively high voltages ( $5V \rightarrow$  hundreds of Volts)
- FETs floating w.r.t. ground

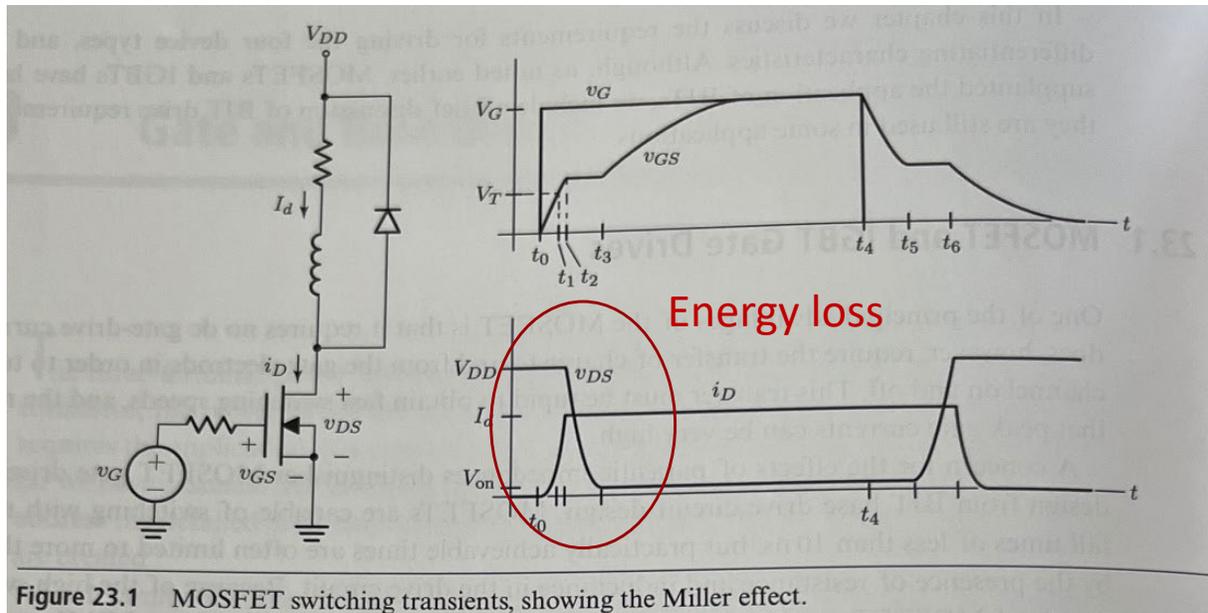


Figure 23.1 MOSFET switching transients, showing the Miller effect.

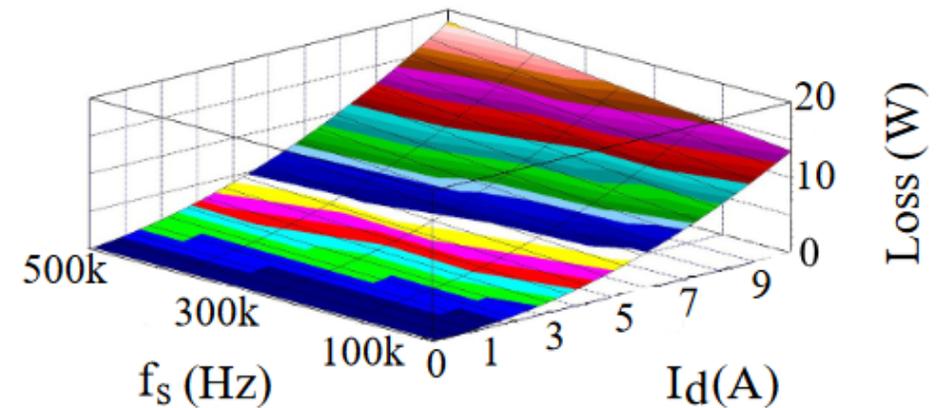


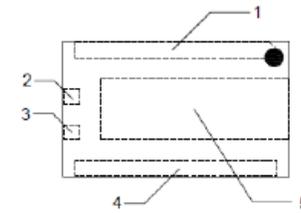
Figure 10. Behavior of switching and conduction losses in MOSFET IRFP460.

# Considerations after PCB prototyping

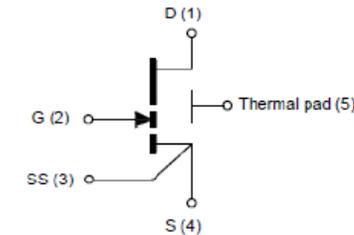
- Commercial transistors not tailored for our applications
  - Much higher  $I_D$  and  $V_{DS,max}$  than needed
  - Higher  $C_{gs}$  than desired  $\rightarrow$  limits frequency of operation
- Commercial resonators not tailored for this application
  - Higher than expected  $R_x$   $\rightarrow$  limits efficiency
  - Difficult to mount/anchor  $\rightarrow$  spurious modes, losses
  - Power handling not understood
- PCB high frequency behavior will be limited by parasitics
  - Need to scale to higher frequency for high Q resonator
  - Frequency drift of drive circuitry affects boost ratio



Package Outline



Circuit Symbol



<https://www.infineon.com/assets/row/public/documents/24/49/infineon-gs61008p-datasheet-en.pdf>

- GaN FET:
  - $I_D = 90A$  !
  - $R_{on} = 7\text{ m}\Omega$  !
  - But  $C_{in} = 600\text{pF}$  /  $Q_g = 8\text{nC}$
- Gate charge and risetime relationship:
  - Desired risetime: 10ns
  - $8\text{ nC} / 10\text{ ns} = \mathbf{0.8A}$  into gate!

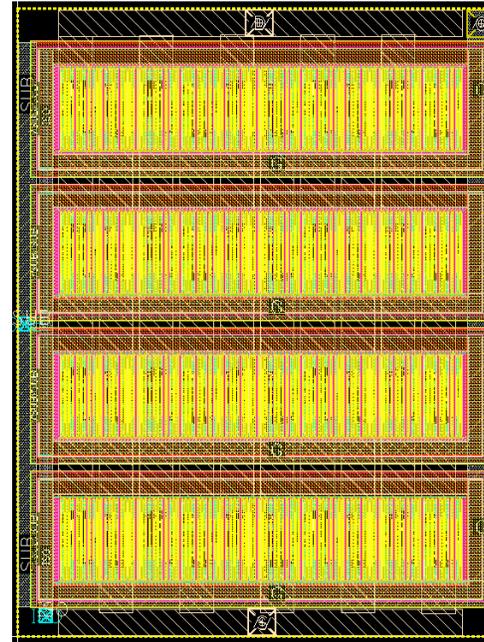
# CMOS v. DMOS

- Smaller L reduces  $R_{on}$

Double-diffused MOSFET

$$R_{on} = \frac{1}{\mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})}$$

- Use lowest  $BV_{DS}$  possible for the application
- (Other processes available ...)



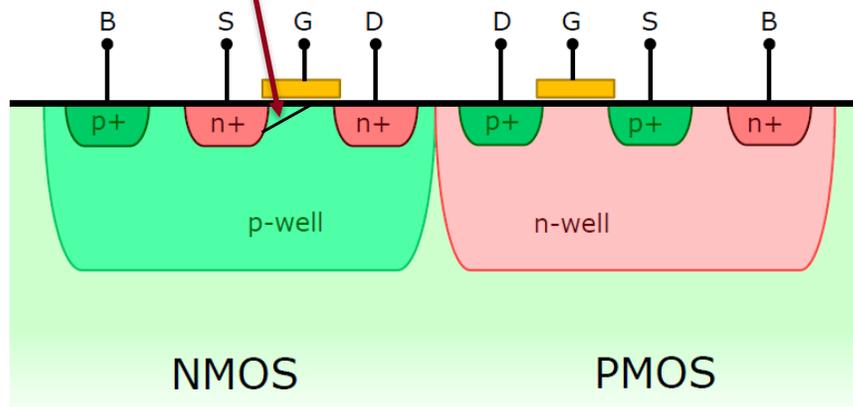
Single 6V FET layout in BCD (bipolar-CMOS-DMOS) process

Many fingers, multiplied

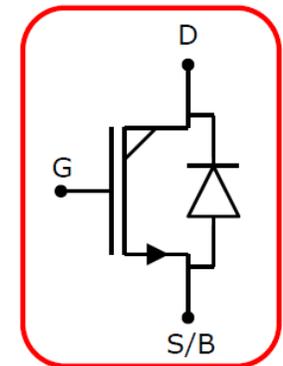
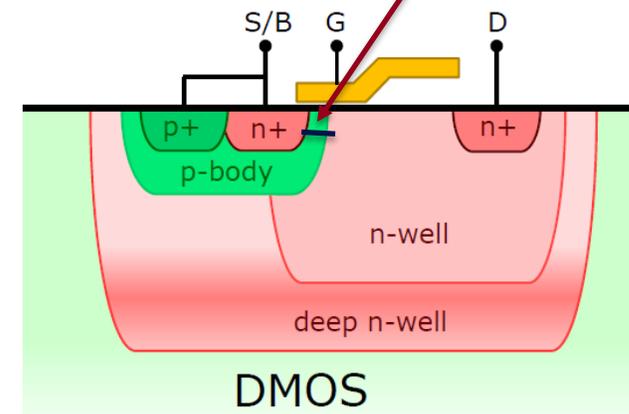
Large area  $\rightarrow$  low  $R_{on}$   
Control  $C_{gs}$

Wide metal  $\rightarrow$  high drain and gate current

Inversion layer



Narrow "L" region

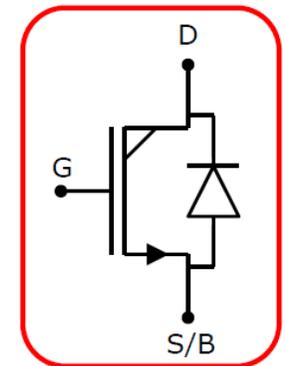
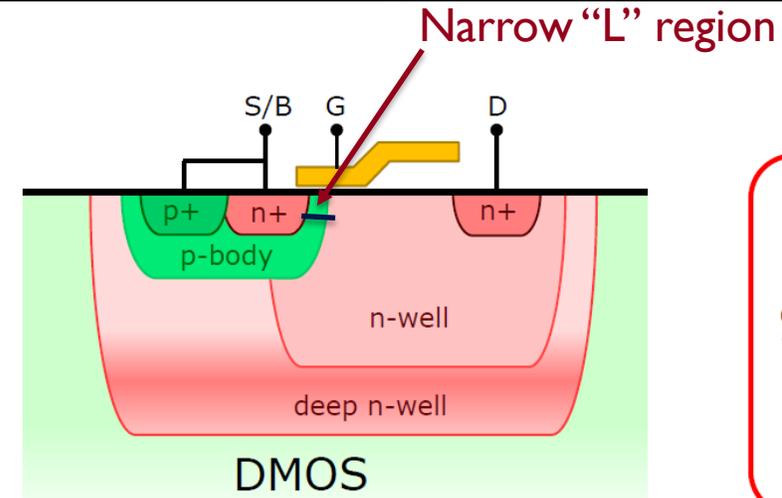
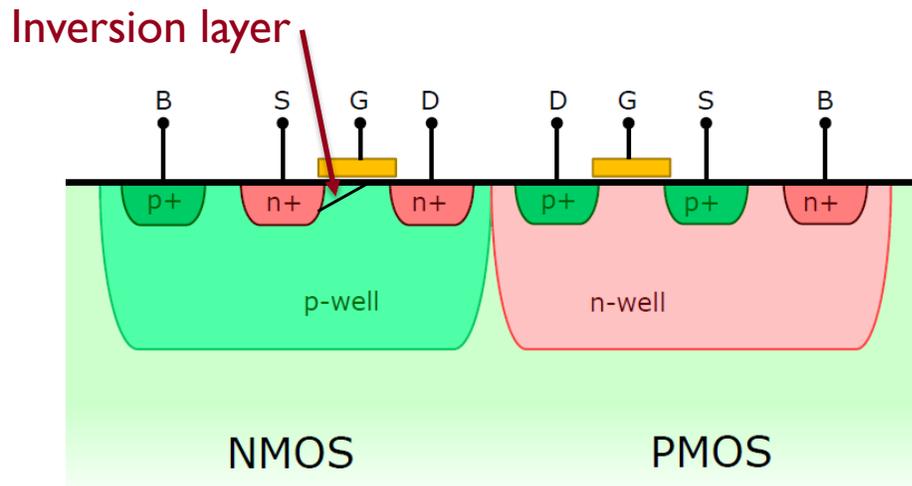
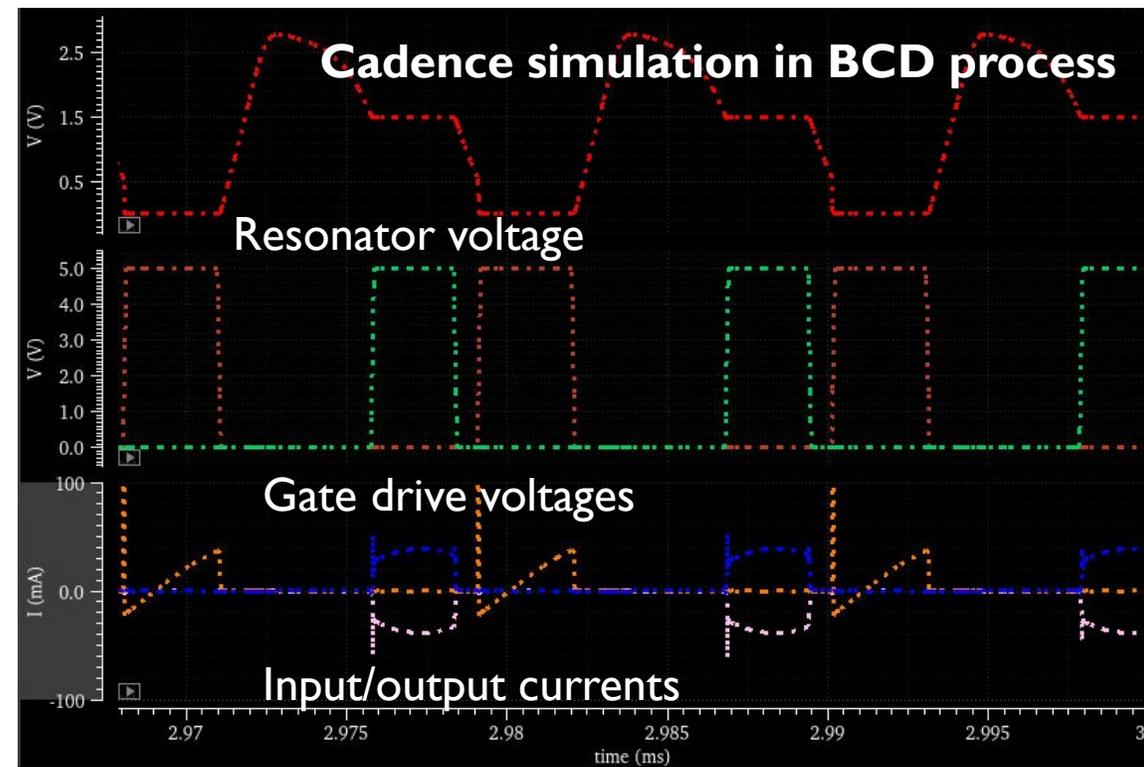


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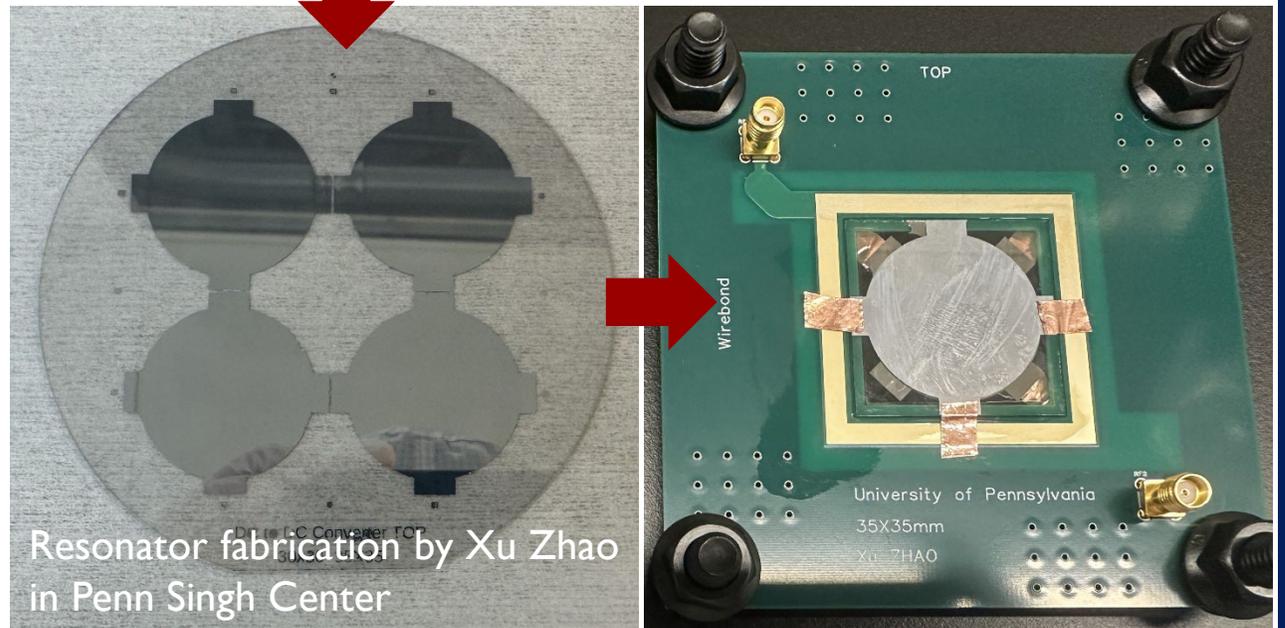
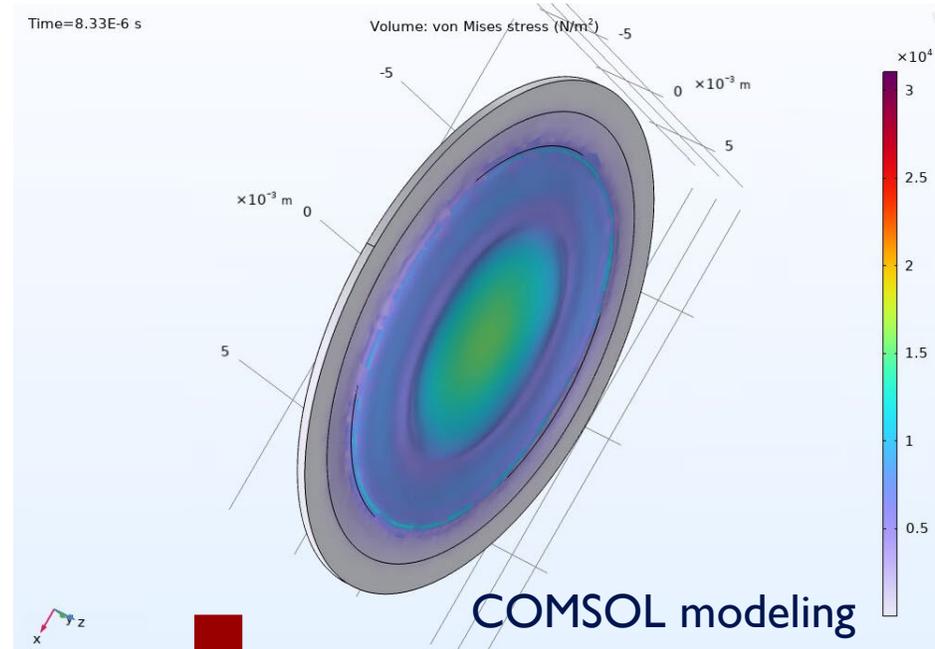
$$R_{on} = \frac{1}{\mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})}$$

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- (Other processes available ...)

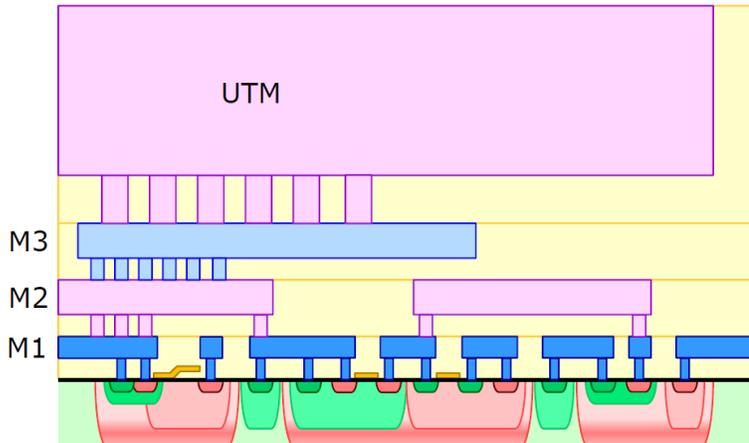


# Resonator design

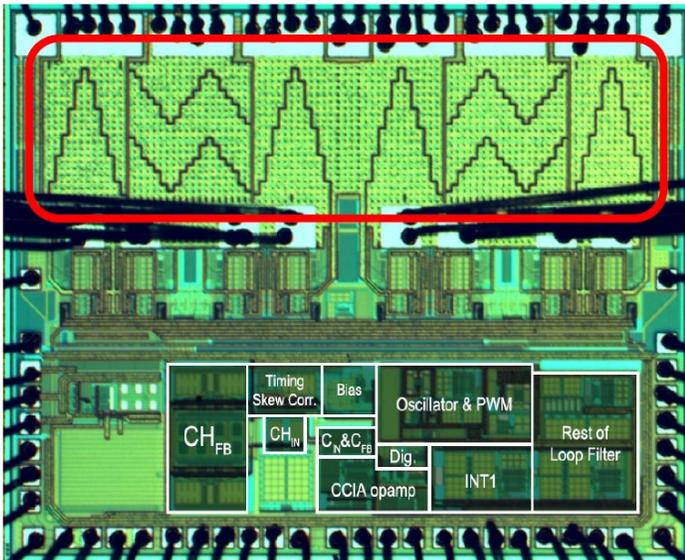
- Spurious mode avoidance: careful electrode design, easier to control over larger inductive region
- Overtone resonators: optimize resonator impedance to load impedance
- Mass augmentation: increases effective inductance, but need to be mindful of series  $R_x$
- Lithium niobate:
  - high Q
  - In shear mode: higher  $K^2$  (electromechanical coupling), no thermoelastic heating (no tension and compression forces)
- Piezoelectric transformers: historically have been used for high voltage gain, but few miniaturized examples, and drive circuitry may need to be improved



# Packaging considerations



Marco Berkhout, Tutorial: Analog Circuit Design in Bipolar-CMOS-DMOS (BCD) Technologies, <https://ieeexplore.ieee.org/document/11005819>



- Must consider wirebonding for higher current applications
- Consider effect on energy transfer, resonator performance

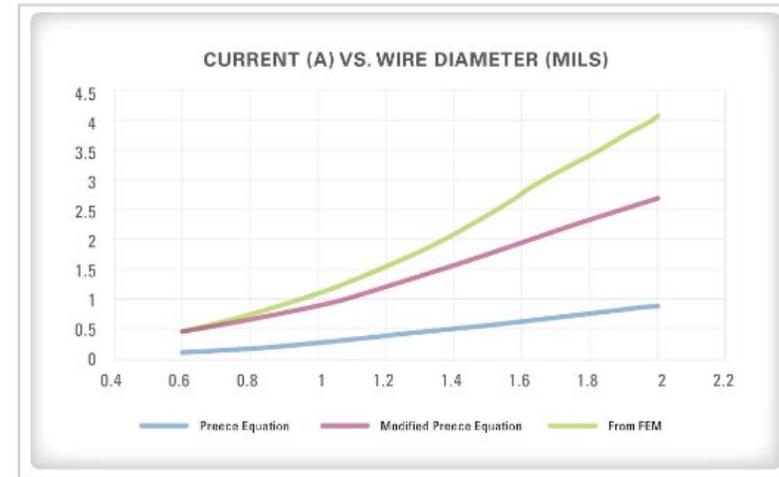
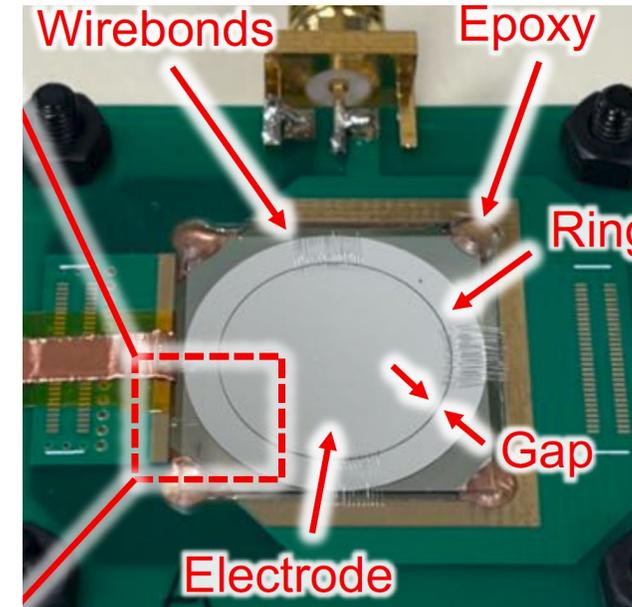


Figure 2: Current-carrying capability of 1-mm-long gold wire using FEM and the Preece equations

Renesas Corporation, ESTIMATING BOND WIRE CURRENT-CARRYING CAPACITY, Power Systems Design July/Aug 2012. (Retrieved from Renesas website)



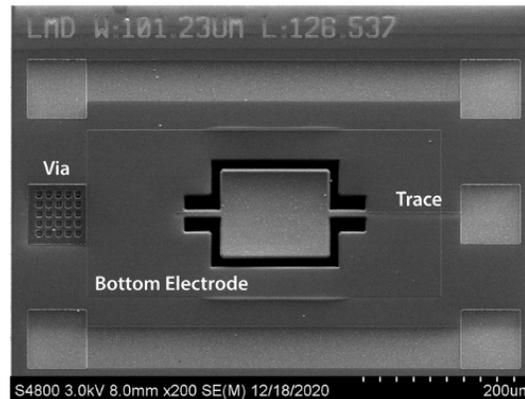
# Summary

	Volume	ASIC integration	Voltage regulation	Power	Efficiency	EMI	Rad. Tolerant	Mag. Tolerant
<b>Inductor</b>	largest	difficult	wide range	medium - high	limited range	most	yes	no
<b>SC</b>	smaller	yes	fixed ranges	wide range	limited range	less	yes	yes
<b>Piezo</b>	smaller	yes	wide range	wide range	to explore	less	to explore	to explore

- This research presents an opportunity for miniaturized power converters tailored for future detector applications

- Possibility of hybrid converters (SC+PR), more exotic technologies (ferroelectric capacitors)

- Opportunities for further miniaturization
- But need to understand high frequency control



Example of MEMS resonator

G. Esteves, T. Young, Z. Tgan, S. Yen, T. Bauer, M. Henry, R. Olsson, "Al 0.68 Sc 0.32 N Lamb wave resonators with electromechanical coupling coefficients near 10.28%", Appl. Phys. Lett. 118, 171902 (2021); doi: 10.1063/5.0047647

- Potential application of boost converters: Silicon photomultipliers (SiPM)
  - Bias ~50-70V, very low current

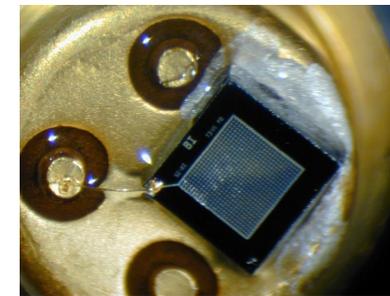


Image: [https://en.wikipedia.org/wiki/Silicon\\_photomultiplier](https://en.wikipedia.org/wiki/Silicon_photomultiplier)

- Applications of buck converters:
  - Nearly ubiquitous
  - Unique environments (magnetic tolerant, small form factor)

Thank you!

